

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|--|---|------------------|---------|------------------|
| L1 | 5280 | 438/592,682,527,530,597,301.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:40 |
| L2 | 490 | 1 and (silicid\$6 near3 anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:42 |
| L3 | 411 | 2 and implant\$6 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:43 |
| L4 | 31 | 3 and (transistor with (metal adj layer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:46 |
| L5 | 12 | 3 and (transistor with substrate with (metal adj layer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:46 |
| S1 | 769062 | transistor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:51 |
| S2 | 5900 | transistor with (metal adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:53 |
| S3 | 68 | transistor with ((metal adj layer) with silicid\$6 with anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:57 |
| S4 | 1281 | ((metal adj layer) with silicid\$6 with anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:58 |
| S5 | 15 | S4 and (remov\$4 unsilicid\$4 metal) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2006/01/26 11:47 |

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|----|----|--------------------------------------|---|------|----|------------------|
| S6 | 11 | S5 and (ion implant\$6) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/26 11:46 |
| S7 | 12 | S5 and (ion near3 implant\$6) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/26 11:47 |
| S8 | 7 | S4 and (remov\$4 unsilicid\$4 metal) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/01/26 11:47 |
| S9 | 5 | S8 and (ion near3 implant\$6) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:39 |